## DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $\mathrm{V}_{\text {(BR)CEO }}=60 \mathrm{~V}$
- DC Current Gain-
: $\mathrm{h}_{\text {FE }}=750$ (Min) @ $\mathrm{Ic}=1.5 \mathrm{~A}$
- Complement to Type BD678
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


## APPLICATIONS

- Designed for use as output devices in complementary general-purpose amplifier applications.


## ABSOLUTE MAXIMUM RATINGS( $\mathrm{T}_{\mathrm{a}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| SYMBOL | PARAMETER | VALUE | UNIT |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\text {CBO }}$ | Collector-Base Voltage | 60 | V |
| $\mathrm{~V}_{\text {CEO }}$ | Collector-Emitter Voltage | 60 | V |
| $\mathrm{~V}_{\text {EBO }}$ | Emitter-Base Voltage | 5 | V |
| $\mathrm{I}_{\mathrm{C}}$ | Collector Current-Continuous | 4 | A |
| $\mathrm{I}_{\mathrm{B}}$ | Base Current | 0.1 | A |
| $\mathrm{P}_{\mathrm{C}}$ | Collector Power Dissipation <br> $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 40 | W |
| $\mathrm{~T}_{\mathrm{i}}$ | Junction Temperature | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature Range | $-55 \sim 150$ | ${ }^{\circ} \mathrm{C}$ |

## THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
| :---: | :---: | :---: | :---: |
| Rth j-c | Thermal Resistance, Junction to Case | 3.13 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |


isc Silicon NPN Darlington Power Transistor

## ELECTRICAL CHARACTERISTICS

$\mathrm{T}=25^{\circ} \mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {(BR)CEO }}$ | Collector-Emitter Breakdown Voltage | $\mathrm{I}_{\mathrm{C}}=50 \mathrm{~mA} ; \mathrm{I}_{\mathrm{B}}=0$ | 60 |  | V |
| $\mathrm{V}_{\text {CE(sat) }}$ | Collector-Emitter Saturation Voltage | $\mathrm{I}_{\mathrm{C}}=1.5 \mathrm{~A} ; \mathrm{I}_{\mathrm{B}}=30 \mathrm{~mA}$ |  | 2.5 | V |
| $V_{\text {bE(on) }}$ | Base-Emitter On Voltage | $\mathrm{I}_{\mathrm{C}}=1.5 \mathrm{~A} ; \mathrm{V}_{\mathrm{CE}}=3 \mathrm{~V}$ |  | 2.5 | V |
| Iceo | Collector Cutoff Current | $V_{C E}=60 \mathrm{~V} ; \mathrm{I}_{\mathrm{B}}=0$ |  | 0.5 | mA |
| Icbo | Collector Cutoff Current | $\begin{aligned} & V_{C B}=60 V ; I_{E}=0 \\ & V_{C B}=60 V ; I_{E}=0 ; T_{C}=100^{\circ} \mathrm{C} \end{aligned}$ |  | $\begin{aligned} & 0.2 \\ & 2.0 \end{aligned}$ | mA |
| $\mathrm{I}_{\text {ebo }}$ | Emitter Cutoff Current | $V_{E B}=5 \mathrm{~V} ; \mathrm{I}^{\prime}=0$ |  | 2.0 | mA |
| $\mathrm{hfE}^{\text {F }}$ | DC Current Gain | $\mathrm{I}_{\mathrm{C}}=50 \mathrm{~mA} ; \mathrm{V}_{\text {CE }}=3 \mathrm{~V}$ | 750 |  |  |
| $h_{\text {FE }}$ | DC Current Gain | $\mathrm{IC}_{\mathrm{C}}=1.5 \mathrm{~A} ; \mathrm{V}_{\text {CE }}=3 \mathrm{~V}$ | 750 |  |  |
| $h_{\text {FE }}$ | DC Current Gain | $\mathrm{I}_{\mathrm{C}}=4 \mathrm{~A} ; \mathrm{V}_{\text {CE }}=3 \mathrm{~V}$ | 1000 |  |  |

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